

Pawel Podemski

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

34
papers

350
citations

11
h-index

17
g-index

41
ext. papers

387
ext. citations

2.8
avg, IF

2.59
L-index

#	Paper	IF	Citations
34	Spin memory effect in charged single telecom quantum dots: erratum. <i>Optics Express</i> , 2021 , 29, 36460	3.3	
33	Spin memory effect in charged single telecom quantum dots. <i>Optics Express</i> , 2021 , 29, 34024-34034	3.3	2
32	Interplay between emission wavelength and s-p splitting in MOCVD-grown InGaAs/GaAs quantum dots emitting above 1.3 μm . <i>Applied Physics Letters</i> , 2020 , 116, 023102	3.4	6
31	Single dot photoluminescence excitation spectroscopy in the telecommunication spectral range. <i>Journal of Luminescence</i> , 2019 , 212, 300-305	3.8	6
30	Excited states of neutral and charged excitons in single strongly asymmetric InP-based nanostructures emitting in the telecom C band. <i>Physical Review B</i> , 2019 , 100,	3.3	6
29	Optimizing the InGaAs/GaAs Quantum Dots for 1.3 μm Emission. <i>Acta Physica Polonica A</i> , 2017 , 132, 386-390		5
28	Probing the carrier transfer processes in a self-assembled system with In _{0.3} Ga _{0.7} As/GaAs quantum dots by photoluminescence excitation spectroscopy. <i>Superlattices and Microstructures</i> , 2016 , 93, 214-220	2.8	
27	Energy Transfer Processes in InAs/GaAs Quantum Dot Bilayer Structure. <i>Acta Physica Polonica A</i> , 2016 , 129, A-59-A-61	0.6	2
26	Probing the excitonic states of site-controlled GaN nanowire quantum dots. <i>Nano Letters</i> , 2015 , 15, 1047-51	7.5	9
25	Measurement of an exciton Rabi rotation in a single GaN/Al(x)Ga(1-x)N nanowire-quantum dot using photoluminescence spectroscopy: evidence for coherent control. <i>Physical Review Letters</i> , 2013 , 111, 057401	7.4	25
24	Temperature Dependent Photoluminescence Excitation Spectroscopy of GaN Quantum Dots in Site Controlled GaN/AlGaN Nanowires. <i>Japanese Journal of Applied Physics</i> , 2013 , 52, 08JL02	1.4	6
23	Electronic Structure of Elongated In _{0.3} Ga _{0.7} As/GaAs Quantum Dots. <i>Acta Physica Polonica A</i> , 2013 , 124, 809-812	0.6	
22	GaAs-Based Quantum Well Exciton-Polaritons beyond 1 μm . <i>Acta Physica Polonica A</i> , 2013 , 124, 817-820	0.6	1
21	Photoluminescence Excitation Spectroscopy on Single GaN Quantum Dots. <i>Applied Physics Express</i> , 2013 , 6, 012102	2.4	11
20	Multiexcitonic emission from single elongated InGaAs/GaAs quantum dots. <i>Journal of Applied Physics</i> , 2012 , 111, 063522	2.5	2
19	Height-driven linear polarization of the surface emission from quantum dashes. <i>Semiconductor Science and Technology</i> , 2012 , 27, 105022	1.8	12
18	Carrier trapping and luminescence polarization in quantum dashes. <i>Physical Review B</i> , 2012 , 85,	3.3	34

17	On the mechanisms of energy transfer between quantum well and quantum dashes. <i>Journal of Applied Physics</i> , 2012 , 112, 033520	2.5	6
16	Hole Subband Mixing and Polarization of Luminescence from Quantum Dashes: A Simple Model. <i>Acta Physica Polonica A</i> , 2011 , 119, 633-636	0.6	11
15	Temperature Dependence of Photoluminescence from Epitaxial InGaAs/GaAs Quantum Dots with High Lateral Aspect Ratio. <i>Acta Physica Polonica A</i> , 2011 , 120, 883-887	0.6	5
14	On the applicability of a few level rate equation model to the determination of exciton versus biexciton kinetics in quasi-zero-dimensional structures. <i>Journal of Applied Physics</i> , 2010 , 108, 033507	2.5	10
13	Excitonic complexes in InGaAs/GaAs quantum dash structures. <i>Journal of Physics: Conference Series</i> , 2010 , 245, 012054	0.3	2
12	Orientation dependent emission properties of columnar quantum dash laser structures. <i>Applied Physics Letters</i> , 2009 , 94, 241113	3.4	12
11	Optically pumped lasing from a single pillar microcavity with InGaAs/GaAs quantum well potential fluctuation quantum dots. <i>Journal of Applied Physics</i> , 2009 , 105, 053513	2.5	3
10	Electromodulation spectroscopy of In _{0.53} Ga _{0.47} As/In _{0.53} Ga _{0.23} Al _{0.24} As quantum wells. <i>Superlattices and Microstructures</i> , 2009 , 46, 425-434	2.8	2
9	Immersion Layer in Columnar Quantum Dash Structure as a Polarization Insensitive Light Emitter at 1.55 μ m. <i>Applied Physics Express</i> , 2009 , 2, 061102	2.4	4
8	Columnar quantum dashes for an active region in polarization independent semiconductor optical amplifiers at 1.55 μ m. <i>Applied Physics Letters</i> , 2008 , 93, 171910	3.4	19
7	Photoluminescence from a single InGaAs epitaxial quantum rod. <i>Applied Physics Letters</i> , 2008 , 92, 021901	3.4	18
6	Contactless modulated reflectivity of quasi 0D self-assembled semiconductor structures. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2007 , 204, 400-411	1.6	1
5	Efficient energy transfer in InAs quantum dash based tunnel-injection structures at low temperatures 2007 ,		3
4	Experimental evidence on quantum well-quantum dash energy transfer in tunnel injection structures for 1.55 μ m emission. <i>Applied Physics Letters</i> , 2007 , 90, 081915	3.4	24
3	On the tunnel injection of excitons and free carriers from In _{0.53} Ga _{0.47} As/In _{0.53} Ga _{0.23} Al _{0.24} As quantum well to InAs/In _{0.53} Ga _{0.23} Al _{0.24} As quantum dashes. <i>Applied Physics Letters</i> , 2006 , 89, 061902	3.4	15
2	Thermal quenching of photoluminescence from InAs/In _{0.53} Ga _{0.23} Al _{0.24} As/InP quantum dashes with different sizes. <i>Applied Physics Letters</i> , 2006 , 89, 151902	3.4	21
1	Photoreflectance-probed excited states in InAs/InGaAlAs quantum dashes grown on InP substrate. <i>Applied Physics Letters</i> , 2006 , 89, 031908	3.4	32